HL8319E/G

GaAIAs LD

Description

T-41-05

The HL8319E/G are high-power 0.8 µm band GaAlAs laser diodes with a double heterojunction structure. Their internal circuit configuration is suited for operation on a single negative supply voltage. They are suitable as light sources for optical disk memories and various other types of optical equipment. Hermetic sealing of the package assures high reliability.

Features

- Infrared light output: $\lambda p = 810$ to 850 nm Typ.
- High power: continuous wave operation at 40 mW, pulsed operation at 50 mW
- Built-in monitor photodiode
- Single longitudinal mode
- Low astigmatism: $A_s = 3 \mu m$ Typ.

Absolute Maximum Ratings ($T_C = 25^{\circ}C$)

| Item | Symbol | Rated Value | Units |
|----------------------------|----------------------------|----------------|-------|
| Optical output power | Po | 40 | mW |
| Pulse optical output power | P _{O (pulse)} 50* | | mW |
| LD reverse voltage | V _{R (LD)} | 2 | V |
| PD reverse voltage | V _{R (PD)} | 30 | V |
| Operating temperature | T _{opr} | -10 to +60 | °C |
| Storage temperature | T _{stg} | -40 to +85 | °C |

Maximum 50% duty cycle, maximum 1 µs pulse width

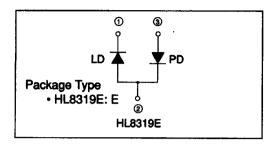
Optical and Electrical Characteristics (T_C = 25°C)

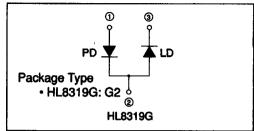
| Item | Symbol | Min | Тур | Max | Units | Test Conditions |
|---------------------------------|-----------------|-----|-----|-----|-------|--|
| Optical output power | Po | 40 | _ | _ | mW | Kink free |
| Threshold current | I _{th} | _ | 40 | 70 | mA | |
| Slope efficiency | η | 0.4 | 0.7 | 0.9 | mW/mA | 24 (mW) I (32 mW) - I (8 mW) |
| Lasing wavelength | λρ | 810 | 830 | 850 | nm | P _O = 40 mW |
| Beam divergence (parallel) | θ _{//} | 8 | 11 | 14 | deg. | P _O = 40 mW, FWHM |
| Beam divergence (perpendicular) | θ_ | 18 | 25 | 32 | deg. | P _O = 40 mW, FWHM |
| Monitor current | Is | 40 | 100 | 240 | μА | $P_0 = 4 \text{ mW}, V_{R (PD)} = 5 \text{ V}$ |
| Astigmatism | As | _ | _ | 10 | μm | P _O = 4 mW, NA = 0.4 |

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Internal Circuit





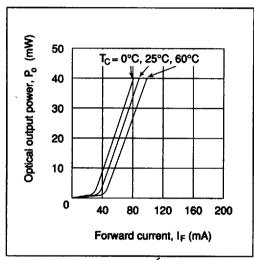


Figure 1 Optical Output Power vs. Forward Current

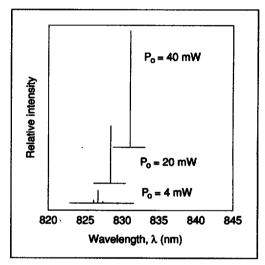


Figure 2 Lasing Spectrum

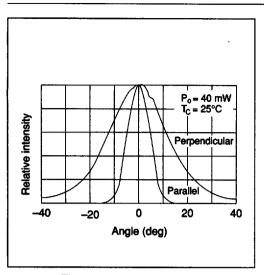


Figure 3 Far Field Pattern

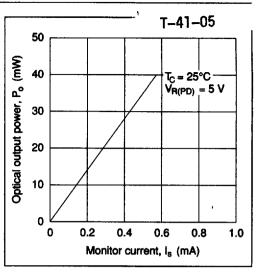


Figure 4 Monitor Current vs. Optical Output Power

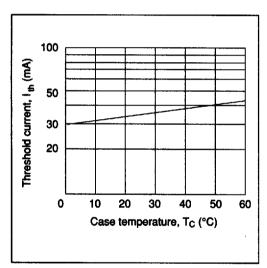


Figure 5 Temperature Dependence of Threshold Current

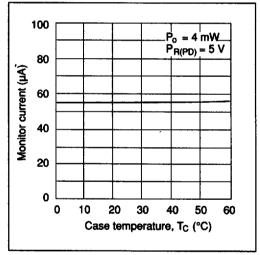
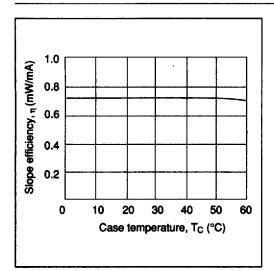


Figure 6 Temperature Dependence of Monitor Current

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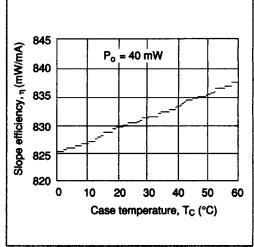
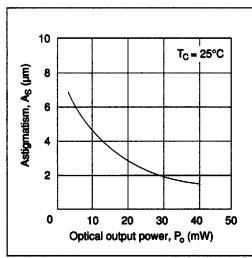


Figure 7 Temperature Dependence of Slope Efficiency

Figure 8 Temperature Dependence of Lasing Wavelength



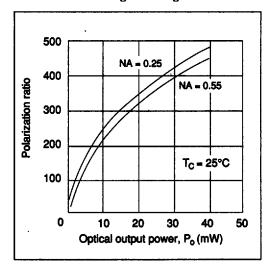


Figure 9 Optical Output Power Dependence of Astigmatism

Figure 10 Optical Output Power Dependence of Polarization Ratio

Section 6 Reliability

This section covers points which particularly affect the operating life light emitting devices, and provides some examples which should be studied before proceeding with your system design.

6.1 Characteristic Drift

When optical emission devices such as the LD or IRED are operated in the forward mode, crystal defects (point defects and dislocations) propagate in the active region of the crystal.

These crystal defects cause optical emission characteristics (optical output power, threshold current, etc.) to drift, and ultimately lead to the end of the device's useful operating life. Figure 6-1 shows an example of drift in the optical output power vs current characteristic of a LD. From t_1 to t_4 , the threshold current increases and the slope efficiency declines. The end of useful operating life is defined as the point where the operating current becomes 1.5 times of its initial value.

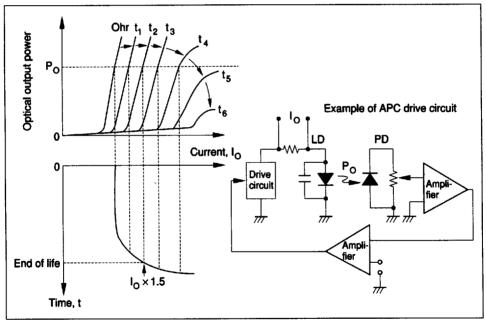


Figure 6-1 Example of Drift in LD Optical Output Power vs. Current Characteristic

6.2 Derating T-90-40

LDs and IREDs have a strong temperature dependence of lifetime. Thus, the expected operating life shows an exponential decrease with operating temperature. Derating should be employed to keep the rise of junction temperature as small as possible. (See figure 6-2, and 6-3). Figure 6-4 shows the dependence of operating life on optical output power. Please note that this decrease in operating life occurs even at threshold current bias.

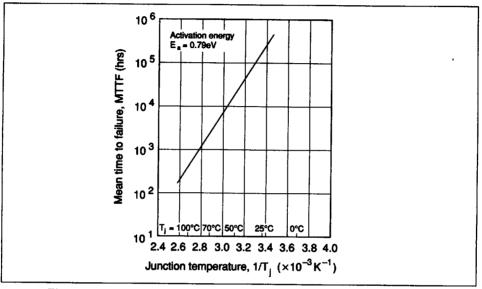


Figure 6-2 LD Mean Time to Failure vs. Junction Temperature (Example)

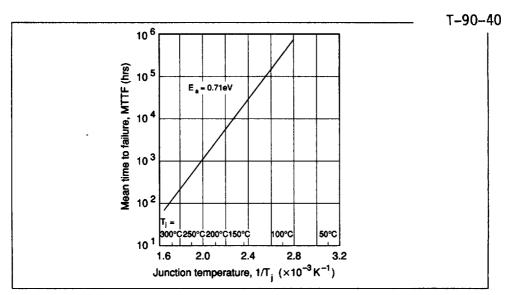


Figure 6-3 IRED Mean Time to Failure vs. Junction Temperature (Example)

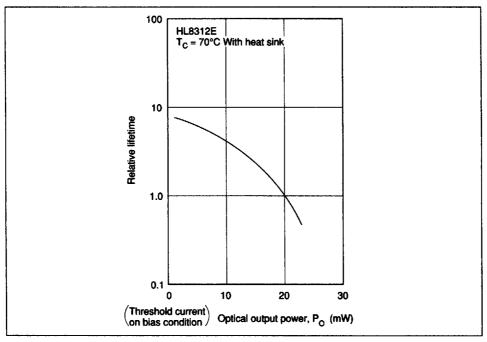


Figure 6-4 LD Operating Life vs. Optical Output Power (Example)

Figure 6-5 shows operating current dependence of IRED lifetime. In particular, when operated in open air at high current, the operating life is drastically affected by the rise in junction temperature due to heat generated by the device. Careful attention must be paid to carrying away excess heat.

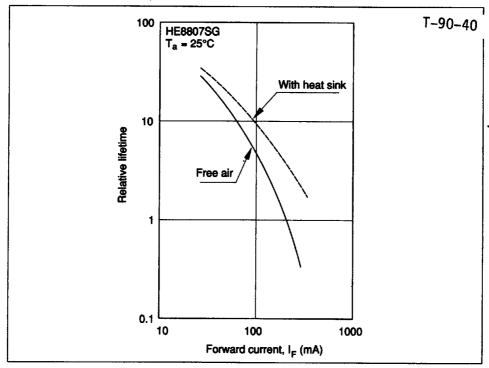


Figure 6-5 IRED Operating Life vs. Forward Current (Example)

6.3 Estimation for Useful Operating Life

The operating life of light emitting devices exhibits the typical wear failure distribution, and thus is generally approximated by the lognormal distribution. Figure 6-6 shows an example distribution for LD operating life. When the temperature derating and optical output power derating discussed in the previous section are also considered, the actual expected operating life under given operating conditions can be estimated.

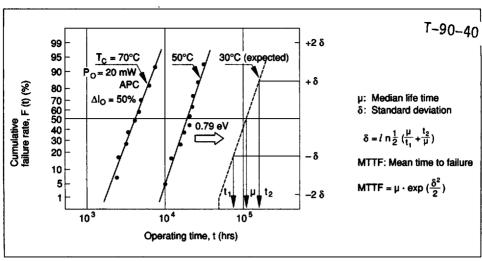


Figure 6-6 Distribution of Expected LD Life (Example)

6.4 Standard Devices Graded by Expected Life

Hitachi classifies IREDs of standard-specifications by life levels and applications as shown in table 6-1. For special requests or further details, please see your Hitachi representative.

Table 6-1 Lifetime and Application for Standard-specification IREDs

| Applications | Expected Life Time | Operating Conditions | Criteria | Applicable Products |
|-----------------------------|-----------------------|---|---------------------------------------|--|
| Auto-focusing still camera | 10 hrs. | I _F = 200 mA | F(t) = 0.1%, $\Delta P_O \le 30\%$ | HE8815VG HE8813VG |
| Auto-focusing VTR camera | 200 hrs. | I _F = 250 mA f = 10 kHz, duty 25% | F(t) = 0.1%, $\Delta P_O \le 30\%$ | HE8815VG |
| Measurement or general use | 1000 hrs. | T _j ≤ P _O 100°C | F(t) = 0.1%, $\Delta P_O \le 30\%$ | HLP series, HE8811, HE8812SG, HE8404SG, HE7601SG |
| Industrial use | 10000 hrs. | T _j ≤ 100°C | F(t) = 1%, $\Delta P_O \le 50\%$ | HE8807 series |
| Communications use | 24000 hrs. | T _j ≤ 100°C | F(t) = 1%, $\Delta P_O \le 50\%$ | HE8403 series, HE1301 series |